

Amendments to the Specification:

Please amend the paragraph at page 26, lines 11-19 as follows:

In the semiconductor laser 1 of the embodiment, as mentioned above, the n-side cladding layer is composed of InGaAsP, whereby the same effects are obtained as when decreasing the equivalent refractive index of an optical waveguide for guiding the light inside the semiconductor laser 1. Consequently, a semiconductor laser of wide active layer width while suppressing generation of the higher lateral ~~harmonic~~ mode can be realized.

Please amend the paragraph at page 32, lines 21-27 as follows:

Even in the case of the semiconductor laser 1 of any embodiment, by lowering the light confinement coefficient in the active layer 5 and first and second SCH layers 4, 6, it is effective to suppress increase of optical loss due to ~~light absorption between valence bands~~ inter valence band absorption (IVBA) in the p-type cladding layer 9, so that laser light of high output can be obtained.